捷多邦,专业PCB打样工厂**TS社250**四**混SL2**51, TSL252 LIGHT-TO-VOLTAGE OPTICAL SENSORS

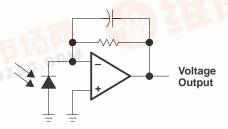
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- Monolithic Silicon IC Containing Photodiode, Operational Amplifier, and Feedback Components
- Converts Light Intensity to Output Voltage
- High Irradiance Responsivity Typically 80 mV/(μW/cm²) at λ_p = 880 nm (TSL250)
- Compact 3-Leaded Clear Plastic Package
- Low Dark (Offset) Voltage . . . 10 mV
 Max at 25°C, V_{DD} = 5 V
- Single-Supply Operation
- Wide Supply-Voltage Range . . . 3 V to 9 V
- Low Supply Current . . . 800 μA Typical at
 V_{DD} = 5 V
- Advanced LinCMOS™ Technology

description

The TSL250, TSL251, and TSL252 are light-to-voltage optical sensors, each combining a photodiode and a transimpedance amplifier (feedback resistor = $16 \text{ M}\Omega$, $8 \text{ M}\Omega$, and $2 \text{ M}\Omega$ respectively) on a single monolithic IC. The output voltage is directly proportional to the light intensity (irradiance) on the photodiode. These devices utilize Texas Instruments silicon-gate LinCMOSTM technology, which provides improved amplifier offset-voltage stability and low power consumption.

functional block diagram



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{DD} (see Note 1)	10 V
Output current, I _O	±10 mA
Duration of short-circuit current at (or below) 25°C (see Note 2)	5 s
Operating free-air temperature range, T _A	−25°C to 85°C
Storage temperature range, T _{stg}	−25°C to 85°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	240°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to GND.

2. Output may be shorted to supply.

recommended operating conditions

	MIN	NOM	MAX	UNIT
Supply voltage, V _{DD}	3	5	9	V
Operating free-air temperature, TA	0		70	°C



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TSL250, TSL251, TSL252 LIGHT-TO-VOLTAGE OPTICAL SENSORS

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electrical characteristics at V_{DD} = 5 V, T_A = 25°C, λp = 880 nm, R_L = 10 k Ω (unless otherwise noted) (see Note 3)

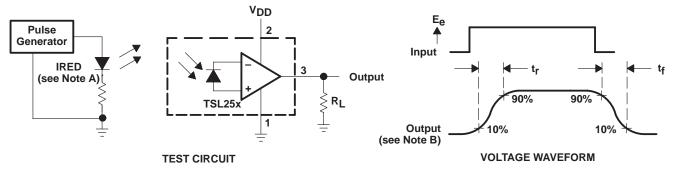
PARAMETER		TEST	TEST TSL250			TSL251				ΓSL252	UNIT	
		CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	ONIT
V_{D}	Dark voltage	$E_e = 0$		3	10		3	10		3	10	mV
Vом	Maximum output voltage swing	$E_e = 2 \text{ mW/cm}^2$	3.1	3.5		3.1	3.5		3.1	3.5		V
	Output voltage	$E_e = 25 \mu\text{W/cm}^2$	1	2	3							
۷o		$E_e = 45 \mu\text{W/cm}^2$				1	2	3				V
		$E_e = 285 \mu W/cm^2$							1	2	3	
	Temperature coefficient of output voltage (VO)	$E_e = 25 \mu W/cm^2$, $T_A = 0^{\circ}C$ to $70^{\circ}C$		±1								
α_{VO}		$E_e = 45 \mu W/cm^2$, $T_A = 0^{\circ}C$ to $70^{\circ}C$					±1					mV/°C
		$E_e = 285 \mu\text{W/cm}^2$, $T_A = 0^{\circ}\text{C} \text{ to } 70^{\circ}\text{C}$								±1		
N _e	Irradiance responsivity	See Note 4		80			45			7		mV/(μW/cm ²)
	Supply current	$E_e = 25 \mu W/cm^2$		900	1600							
IDD		$E_e = 45 \mu\text{W/cm}^2$					900	1600				μΑ
		$E_e = 285 \mu W/cm^2$								900	1600	

NOTES: 3. The input irradiance E_e is supplied by a GaAlAs infrared-emitting diode with λ_p = 880 nm. 4. Irradiance responsivity is characterized over the range V_O = 0.05 to 3 V.

operating characteristics at $T_A = 25^{\circ}C$ (see Figure 1)

DADAMETED	PARAMETER	TEST CONDITIONS	TSL250			TSL251			TSL252			UNIT
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
t _r	Output pulse rise time	$V_{DD} = 5 \text{ V}, \lambda_p = 880 \text{ nm}$		360			90			7		μs
tf	Output pulse fall time	$V_{DD} = 5 \text{ V}, \lambda_p = 880 \text{ nm}$		360			90			7		μs
٧n	Output noise voltage	V _{DD} = 5 V, f = 20 Hz		0.6			0.5			0.4		μV/√Hz

PARAMETER MEASUREMENT INFORMATION



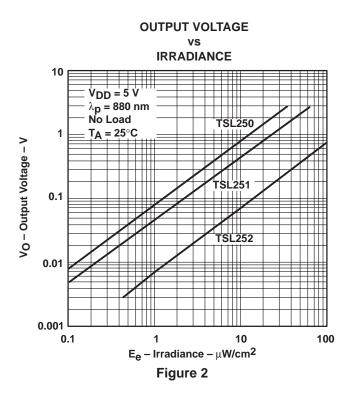
NOTES: A. The input irradiance is supplied by a pulsed GaAlAs infrared-emitting diode with the following characteristics: λ_p = 880 nm, $t_r < 1 \mu s$, $t_f < 1 \mu s$.

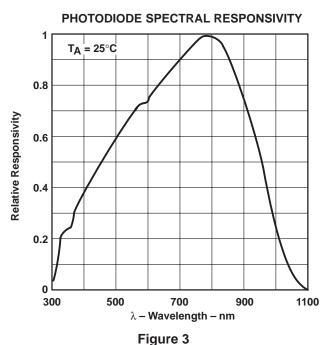
B. The output waveform is monitored on an oscilloscope with the following characteristics: $t_{\Gamma} < 100$ ns, $Z_{i} \ge 1$ MHz, $C_{i} \le 20$ pF.

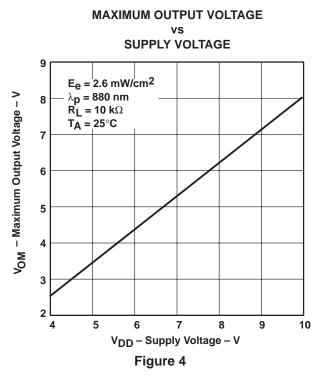
Figure 1. Switching Times

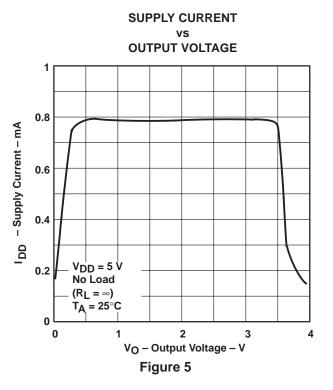


TYPICAL CHARACTERISTICS









TYPICAL CHARACTERISTICS

NORMALIZED OUTPUT VOLTAGE

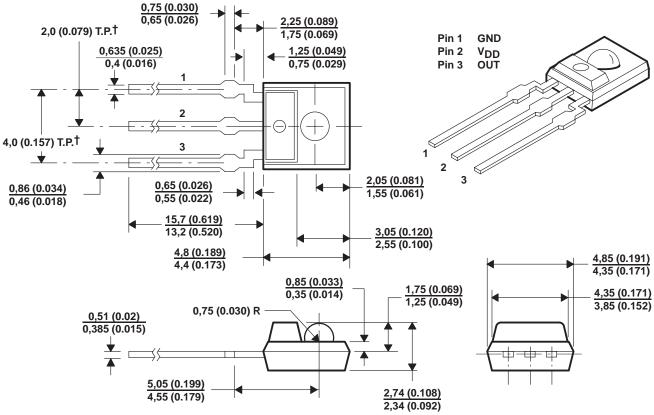
ANGULAR DISPLACEMENT 8.0 V_O - Normalized Output Voltage **TSL250** TSL251, 252 0.6 Optical Axis 0.4 0.2 80° **60**° **40**° $\textbf{20}^{\circ}$ **0**° **20**° **40**° **60**° **80**° θ – Angular Displacement

Figure 6

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APPLICATION INFORMATION

The photodiode/amplifier chip is packaged in a clear plastic three-leaded package. The integrated photodiode active area is typically 1,0 mm² (0.0016 in²) for TSL250, 0,5 mm² (0.00078 in²) for the TSL251, and 0,26 mm² (0.0004 in²) for the TSL252.



[†] True position when unit is installed.

NOTES: A. All linear dimensions are in millimeters (inches).
B. This drawing is subject to change without notice.

Figure 7. Mechanical Data



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